

**CLAIM AMENDMENTS:**

Please amend claims 1, 20 and 21, and cancel claims 10-19 and 27-36 as follows:

1. (Currently Amended) A three dimension (3D) polysilicon read only memory (ROM), at least comprising:

a silicon substrate;

an isolated silicon dioxide ( $\text{SiO}_2$ ) layer, which is deposited on the silicon substrate;

a N-Type heavily doped ( $\text{N}^+$ ) polysilicon layer, which is deposited on the isolated  $\text{SiO}_2$  layer and is further ~~defined~~ defines a plurality of parallel, separate word lines (WL);

a first oxide layer, which is filled in the space between the word lines;

a dielectric layer, which is deposited on the word lines and the first oxide layer;

a P-Type lightly doped ( $\text{P}^-$ ) polysilicon layer, which is deposited on the dielectric layer and is further ~~defined~~ defines a plurality of parallel, separate bit lines (BL), wherein the bit lines overlap the word lines, from a top view, to form a shape ~~approximately as~~ <sup>that</sup> defines a cross;

at least a neck structure, which are individually formed between ~~the first polysilicon layer and the second polysilicon layer~~ the N-type heavily doped ( $\text{N}^+$ ) polysilicon layer and the P-type lightly doped ( $\text{P}^-$ ) polysilicon layer by ~~isotropy~~ isotropically etching the dielectric layer and using dilute hydrofluoric acid (HF); and

a second oxide layer, which is filled in the space between the bit lines and is on the word lines and the first oxide layer.

AMENDMENT

(10/728,767)

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WJ  
5/25/05